# 5 V, 3 A Current-Mode Constant On-Time Synchronous Buck Regulator

#### **DESCRIPTION**

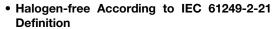
The SiP12107 is a high frequency current-mode constant on-time (CM-COT) synchronous buck regulator with integrated high-side and low-side power MOSFETs. Its power stage is capable of supplying 3 A continuous current at 4 MHz switching frequency. This regulator produces an adjustable output voltage down to 0.6 V from 2.8 V to 5.5 V input rail to accommodate a variety of applications, including computing, consumer electronics, telecom, and industrial.

SiP12107's CM-COT architecture delivers ultra-fast transient response with minimum output capacitance and tight ripple regulation at very light load. No ESR or external ESR network is required for loop stability purpose. The device also incorporates a power saving scheme that significantly increases light load efficiency.

The regulator integrates a full protection feature set, including output overvoltage protection (OVP), output under voltage protection (UVP) and thermal shutdown (OTP). It also has UVLO for input rail and internal soft-start ramp.

The SiP12107 is available in lead (Pb)-free power enhanced MLP-16L package in 3 mm x 3 mm dimension.

#### **FEATURES**





HALOGEN

FREE

- 2.8 V to 5.5 V input voltage
- Adjustable output voltage down to 0.6 V
- 3 A continuous output current
- Programmable switching frequency up to 4 MHz
- 95 % peak efficiency
- Supports all ceramic capacitors No external ESR required
- Ultrafast transient response
- Selectable power saving mode or force current mode
- ± 1 % accuracy
- Pulse-by-pulse current limit
- Scalable with SiP12108 5A
- Fully protected with OTP, SCP, UVP, OVP
- P<sub>Good</sub> Indicator
- Compliant to RoHS Directive 2011/65/EU

#### **APPLICATIONS**

- Notebook computers
- Desktop PCs and servers
- Handheld devices
- POLs for telecom
- Consumer electronics
- Industrial and automation

#### TYPICAL APPLICATION CIRCUIT AND PACKAGE OPTIONS

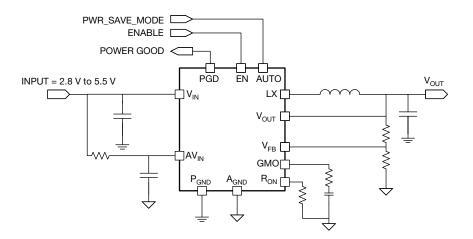


Fig. 1 - Typical Application Circuit for SiP12107



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# Vishay Siliconix

ABSOLUTE MAXIMUM RATINGS						
ELECTRICAL PARAMETER	CONDITIONS	LIMIT	UNIT			
V <sub>IN</sub>	Reference to P <sub>GND</sub>	- 0.3 to 6				
AV <sub>IN</sub>	Reference to A <sub>GND</sub>	- 0.3 to 6				
LX	Reference to P <sub>GND</sub>	- 0.3 to 6	V			
A <sub>GND</sub> to P <sub>GND</sub>		- 0.3 to + 0.3				
All Logic Inputs	Reference to A <sub>GND</sub>	- 0.3 to AV <sub>IN</sub> + 0.3				
TEMPERATURE						
Max. Operating Junction Temperature		150	°C			
Storage Temperature		- 65 to 150	C			
POWER DISSIPATION						
Junction to Ambient Thermal Impedance (R <sub>thJA</sub> )		36.3	°C/W			
Maximum Dawar Dissipation	Ambient Temperature = 25 °C	erature = 25 °C 3.4				
Maximum Power Dissipation	Ambient Temperature = 100 °C	1.3	W			
ESD PROTECTION						
	НВМ	2	kV			

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING RANGE					
ELECTRICAL PARAMETER	MINIMUM	TYPICAL	MAXIMUM	UNIT	
V <sub>IN</sub>	2.8	-	5.5		
AV <sub>IN</sub>	2.8	-	5.5	V/	
LX	- 1	-	5.5	V	
V <sub>OUT</sub>	0.6	-	0.85 x V <sub>IN</sub>		
Ambient Temperature	- 40 to 85			°C	



	TEST CONDITION UNLESS OTHERWISE		LIMITS				
PARAMETER	SYMBOL	<b>SPECIFIED</b> $V_{IN} = AV_{IN} = 3.3 \text{ V}, T_A = -40 ^{\circ}\text{C} \text{ to } 85 ^{\circ}\text{C}$	MIN.	TYP.	MAX.	UNIT	
POWER SUPPLY	<u>'</u>				•		
Power Input Voltage Range	V <sub>IN</sub>		2.8	-	5.5	.,	
Bias Input Voltage Range	AV <sub>IN</sub>		2.8	-	5.5	V	
Input Current	IV <sub>IN_NOLOAD</sub>	Device switching, $I_0 = 0 \text{ A}$ , $R_{on} = 100 \text{ k}\Omega$ , AUTO = Low	-	1000	-	μA	
Shutdown Current	IV <sub>IN_SHDN</sub>	EN = 0 V	-	6	12		
AV <sub>IN</sub> UVLO Threshold	AV <sub>IN</sub> , U <sub>VLO</sub>	AV <sub>IN</sub> rising edge	-	2.55	-	V	
AV <sub>IN</sub> UVLO Hysteresis	U <sub>VLOHYS</sub>			300	-	mV	
PWM CONTROLLER							
Feedback Reference	V	T <sub>A</sub> = 0 °C to + 70 °C	0.594	0.600	0.606		
reedback Reference	V <sub>FB</sub>	T <sub>A</sub> = - 40 °C to + 85 °C	0.591	0.600	0.609	V	
V <sub>FB</sub> Input Bias Current			-	2	200	nA	
Transconductance			-	1	-	mS	
COMP Source Current			-	50	-		
COMP Sink Current			-	50	-	μA	
Switching Frequency Range		Guaranted by design	0.2	-	4	MH	
Minimum On-Time		Guaranted by design	-	50	-		
Minimum Off-Time		$V_{OUT} = 1.2 \text{ V}, R_{ON} = 100 \text{ k}\Omega$	-	120	-	ns	
Soft Start Time			-	1.5	-	ms	
INTEGRATED MOSFETS							
High-Side On Resistance		V 00V	-	56	-		
Low-Side On Resistance		$V_{IN} = 3.3 \text{ V}$	-	33	-	mΩ	
FAULT PROTECTIONS							
Over Current Limit		Inductor valley current	-	4.5	-	Α	
Output OVP Threshold		V The constant to 0.0 V of the constant	-	20	-	%	
Output UVP Threshold		V <sub>FB</sub> with respect to 0.6 V reference	-	- 25	-		
O set Terror and the Books fire		Rising temperature	-	160	-	°C	
Over Temperature Protection		Hysteresis	-	35	-		
POWER GOOD					•		
Devices On and Outland There is a late		V <sub>FB</sub> rising above 0.6 V reference	-	20	-	0/	
Power Good Output Threshold		V <sub>FB</sub> falling below 0.6 V reference	-	- 10	-	%	
Power Good On Resistance			-	30	-	Ω	
Power Good Delay Time			-	6	-	μs	
ENABLE THRESHOLD							
Logic High Level			1.5	-	-	V	
Logic Low Level			-	-	0.4	7 °	



# **FUNCTIONAL BLOCK DIAGRAM**

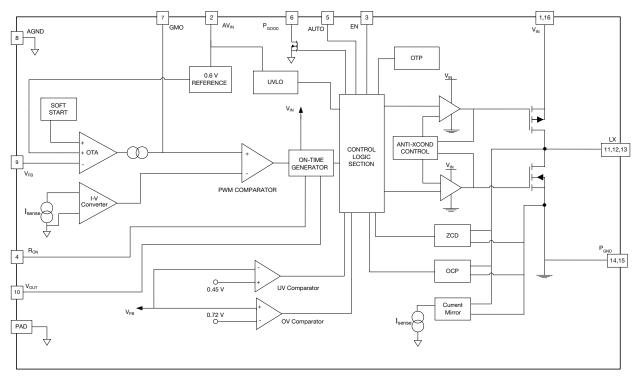
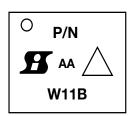


Fig. 2 - SiP12107 Functional Block Diagram

ORDERING INFORMATION				
PART NUMBER	PACKAGE	MARKING (LINE 2: P/N)		
SIP12107DMP-T1-GE3	QFN33-16L	2107		
SIP12107DB	Reference Board			



Format:

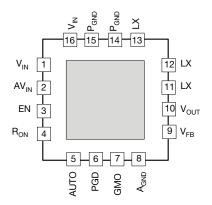
Line 1: Dot

Line 2: P/N

Line 2: Siliconix Logo + ESD Symbol

Line 3: Factory Code + Year Code + Work Week Code + Lot Code

# **PIN CONFIGURATION**

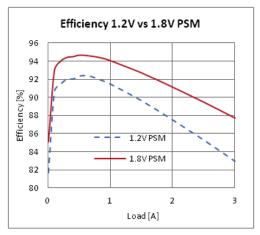


MLPQ 3 x 3 - 16L

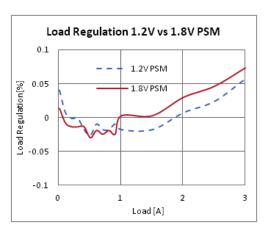
Fig. 3 - SiP12107 Pin Configuration (Top View)

PIN CONFIG	PIN CONFIGURATION						
PIN NUMBER	NAME	FUNCTION					
1	V <sub>IN</sub>	Input supply voltage for power MOS. V <sub>IN</sub> = 2.8 V to 5.5 V					
2	AV <sub>IN</sub>	Input supply voltage for internal circuitry. AV <sub>IN</sub> = 2.8 V to 5.5 V					
3	EN	Enable pin. Enable > 1.5 V					
4	R <sub>ON</sub>	An external resistor between R <sub>ON</sub> and GND sets the switching on time.					
5	AUTO	Sets switching mode AUTO to AV <sub>IN</sub> = PWM, AUTO to GND = light load mode					
6	PGD	Power good output. Open drain.					
7	GMO	Connect to an external RC network for loop compensation and droop function					
8	A <sub>GND</sub>	Analog ground					
9	$V_{FB}$	Feedback voltage. 0.6 V (typ.)					
10	V <sub>OUT</sub>	V <sub>OUT</sub> , output voltage sense connection					
11	LX	Switching output, inductor connection point					
12	LX	Switching output, inductor connection point					
13	LX	Switching output, inductor connection point					
14	P <sub>GND</sub>	Power ground					
15	P <sub>GND</sub>	Power ground					
16	V <sub>IN</sub>	Input supply voltage for power MOS. V <sub>IN</sub> = 2.8 V to 5.5 V					

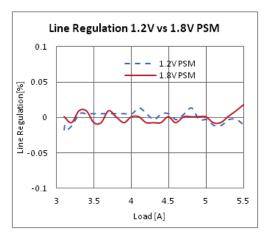
# **ELECTRICAL CHARACTERISTICS** ( $V_{IN} = 3.3 \text{ V}$ , $L = 1 \mu\text{H}$ , $C = 3 \times 22 \mu\text{F}$ , $f_{SW} = 1.2 \text{ MHz}$ unless noted otherwise)



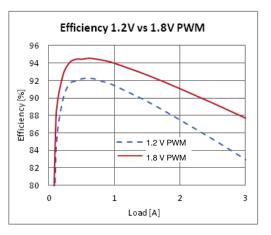
Efficiency vs. IOUT (PSM)



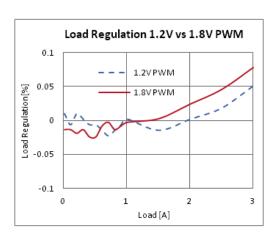
Load Regulation: % of V<sub>OUT</sub> vs. I<sub>OUT</sub> (PSM)



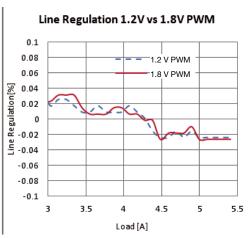
Line Regulation 1.2 VouT Nominal 0 A Load (PSM)



Efficiency vs. I<sub>OUT</sub> (PWM)

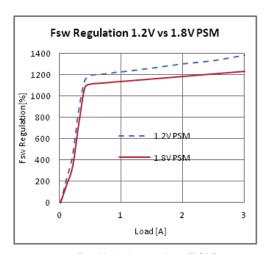


Load Regulation: % of V<sub>OUT</sub> vs. I<sub>OUT</sub> (PWM)

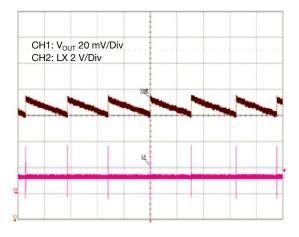


Line Regulation 1.2 V<sub>OUT</sub> at 3 A Load (PWM)

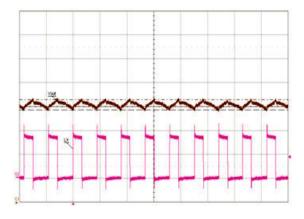




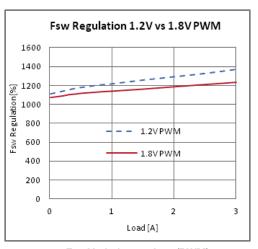
 $F_{SW}$  Variation vs.  $I_{OUT}$  (PSM)



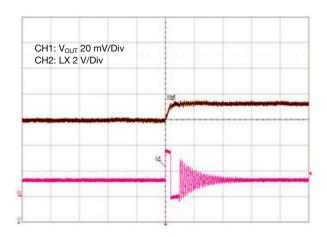
Output Ripple PSM: 0 A Load



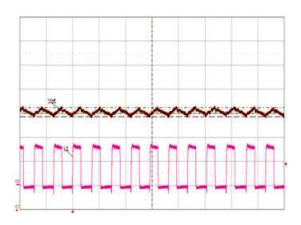
Output Ripple PWM: 0 A Load



F<sub>SW</sub> Variation vs. I<sub>OUT</sub> (PWM)

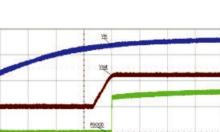


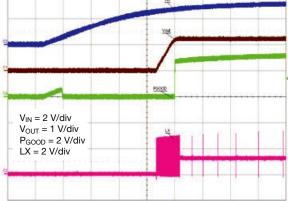
Output Ripple PSM: 0 A Load



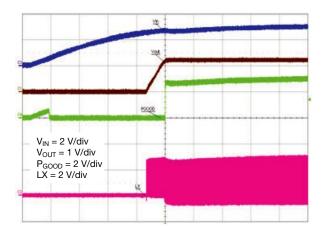
Output Ripple PWM: 3 A Load



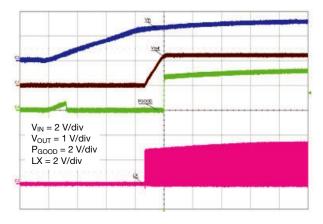




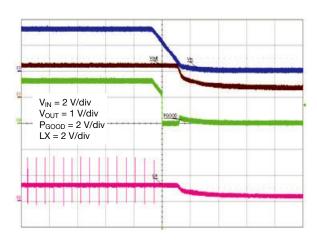
Startup PSM: 0 A Load



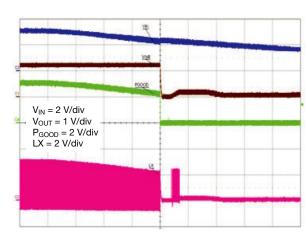
Startup PSM: 3 A Load



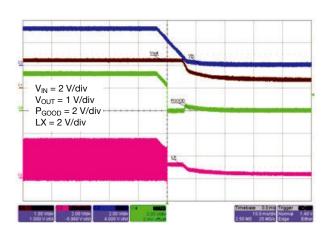
Startup PWM: 0 A Load



Shutdown PSM: 0 A Load

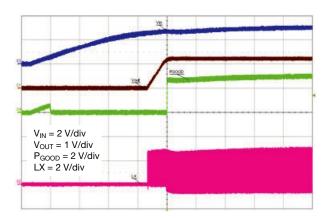


Shutdown PSM: 3 A Load

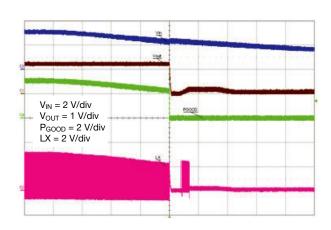


Shutdown PWM: 0 A Load

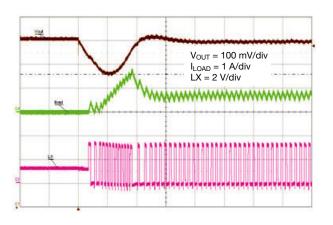




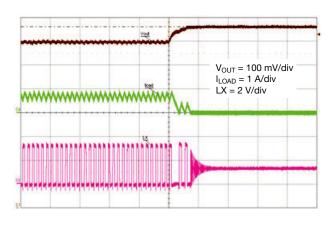
Startup PWM: 3 A Load



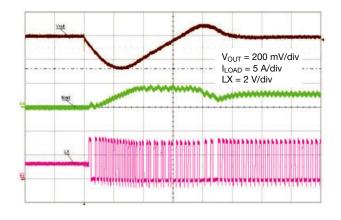
Shutdown PWM: 3 A Load



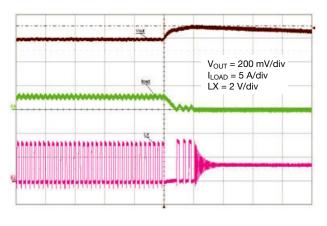
Load Step PSM: 0 A to 1.5 A Load (undershoot)



Load Step PSM 0 A to 1.5 A Load (overshoot)

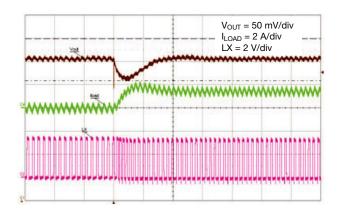


Load Step PSM: 0 A to 3 A Load (undershoot)

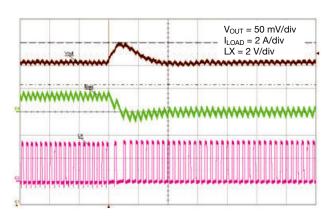


Load Step PSM: 0 A to 3 A Load (overshoot)

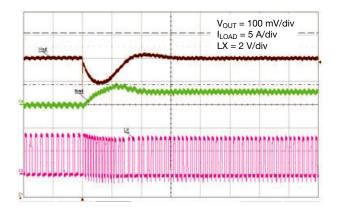




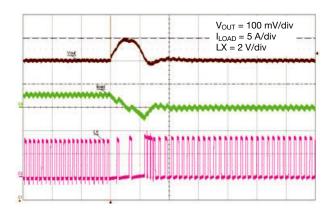
Load Step PWM: 0 A to 1.5 A Load (undershoot)



Load Step PWM 0 A to 1.5 A Load (overshoot)



Load Step PWM: 0 A to 3 A Load (undershoot)



Load Step PWM 0 A to 3 A Load (overshoot)

#### **OPERATIONAL DESCRIPTION**

#### **Device Overview**

SiP12107 is a high-efficiency monolithic synchronous buck regulator capable of delivering up to 3 A continuous current. The device has programmable switching frequency up to 4 MHz. The control scheme is based on current-mode constant-on-time architecture, which delivers fast transient response and minimizes external components. Thanks to the internal current ramp information, no high-ESR output bulk or virtual ESR network is required for the loop stability. This device also incorporates Power-Saving feature by enabling diode emulation mode and frequency foldback as load decrease.

SiP12107 has a full set of protection and monitoring features:

- Over current protection in pulse-by-pulse mode
- Output over voltage protection
- Output under voltage protection with device latch
- Over temperature protection with hysteresis
- Dedicated enable pin for easy power sequencing
- Power Good open drain output

This device is available in MLPQ 3 x 3-16L package to deliver high power density and minimize PCB area.

#### **Power Stage**

SiP12107 integrates a high-performance power stage with a  $\sim$  64 m $\Omega$  p-channel MOSFET and a  $\sim$  33 m $\Omega$  n-channel MOSFET. The MOSFETs are optimized to achieve 95 % efficiency at 2 MHz switching frequency.

The power input voltage ( $V_{IN}$ ) can go up to 5.5 V and down as low as 2.8 V for the power conversion. The logic bias voltage ( $AV_{IN}$ ) ranges from 2.8 V to 5.5 V.

#### **PWM Control Mechanism**

SiP12107 employs a state-of-the-art current-mode COT control mechanism. During steady-state operation, output voltage is compared with internal reference (0.6 V typ.) and the amplified error signal ( $V_{COMP}$ ) is generated on the COMP pin. In the meantime, inductor valley current is sensed, and its slope ( $I_{sense}$ ) is converted into a voltage signal ( $V_{current}$ ) to be compared with  $V_{COMP}$ . Once  $V_{current}$  is lower than  $V_{COMP}$ , a single shot on-time is generated for a fixed time programmed by the external  $R_{ON}$ . Figure 4 illustrates the basic block diagram for CM-COT architecture and figure 5 demonstrates the basic operational principle:

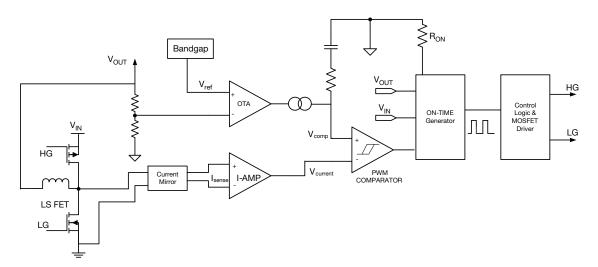


Fig. 4 - CM-COT Block Diagram



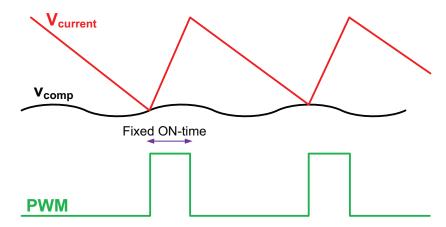


Fig. 5 - CM-COT Operational Principle

The following equation illustrates the relationship between on-time,  $V_{\text{IN}}$ ,  $V_{\text{OUT}}$  and  $R_{\text{ON}}$  value:

$$T_{ON} = R_{ON} \ x \ K \ x \ \frac{V_{OUT}}{V_{IN}}$$
, where K = 9.6 x 10<sup>-12</sup> a constant set internally

Once on-time is set, the pseudo constant frequency is then determined by the following equation:

$$f \text{sw} = \frac{D}{T_{ON}} = \frac{\frac{V_{OUT}}{V_{IN}}}{\frac{V_{OUT}}{V_{IN}} \times R_{ON} \times K} = \frac{1}{R_{ON} \times K}$$

#### **Loop Stability and Compensator Design**

Due to the nature of current mode control, a simple RC network (type II compensator) is required between COMP and A<sub>GND</sub> for loop stability and transient response purpose. General concept of this loop design is to introduce a single zero through the compensator to determine the crossover frequency of overall close loop system.

The overall loop can be broken down into following segments.

Output feedback divider transfer function H<sub>fb</sub>:

$$H_{fb} = \frac{R_{fb2}}{R_{fb1} \times R_{fb2}}$$

Voltage compensator transfer function G<sub>COMP</sub> (s):

$$G_{COMP}(s) = \frac{R_O x (1 + sC_{COMP}R_{COMP})}{(1 + sR_OC_{COMP})} gm$$

Modulator transfer function H<sub>mod</sub> (s):

$$H_{mod}$$
 (s) =  $\frac{1}{AV_1 \times R_{DS(on)}} \times \frac{R_{load} \times (1 + sC_0R_{ESR})}{(1 + sC_0R_{load})}$ 

The complete loop transfer function is given by:

$$H_{mod} \left( s \right) = \frac{{{R_{fb2}}}}{{{R_{fb1}}}\,x\,{R_{fb2}}}\,x\,\frac{{{R_O}}\,x\,(1 + s{C_{COMP}}{R_{COMP}})}{(1 + s{R_O}{C_{COMP}})}gm\,x\,\frac{1}{{A{V_1}}\,x\,{R_{DS(on)}}}\,x\,\frac{{{R_{load}}}\,x\,(1 + s{C_O}{R_{ESR}})}{(1 + s{C_O}{R_{load}})}$$

#### When:

 $C_{COMP}$  = Compensation capacitor  $R_{DS(on)}$  = LS switch resistance

 $R_{COMP}$  = Compensation resistor  $R_{fb1}$  = Feedback resistor connect to LX gm = Error amplifier transconductance  $R_{fb2}$  = Feedback resistor connect to ground

 $R_{load}$  = Load resistance  $R_{O}$  = Output impedance of error amplifier = 20  $M\Omega$ 

 $C_O$  = Output capacitor  $AV_1$  = Voltage to current gain = 3

#### **Power-Saving Mode Operation**

To further improve efficiency at light-load condition, SiP12107 provides a set of innovative implementations to eliminate LS recirculating current and switching losses. The internal Zero Crossing Detector (ZCD) monitors LX node voltage to determine when inductor current starts to flow negatively. In power saving mode (PSM), as soon as inductor valley current crosses zero, the device first deploys diode emulation mode by turning off LS FET. If load further decreases, switching frequency is further reduced

proportional to load condition to save switching losses while keeping output ripple within tolerance. The switching frequency is set by the controller to maintain regulation. At zero load this frequency can go as low as hundreds of Hz.

Whenever fixed frequency PWM operation is required over the entire load span, power saving mode feature can be disabled by connecting AUTO pin to  $V_{\text{IN}}$  or  $AV_{\text{IN}}$ .

#### **OUTPUT MONITORING AND PROTECTION FEATURES**

#### **Output Over-Current Protection (OCP)**

SiP12107 has pulse-by-pulse over-current limit control. The inductor valley current is monitored during LS FET turn-on period through  $R_{DS(on)}$  sensing. After a pre-defined time, the valley current is compared with internal threshold (5 A typ.) to determine the threshold for OCP. If monitored current is higher than threshold, HS turn-on pulse is skipped and LS FET is kept on until the valley current returns below OCP limit.

In the severe over-current condition, pulse-by-pulse current limit eventually triggers output under-voltage protection (UVP), which latches the device off to prevent catastrophic thermal-related failure. UVP is described in the next section. OCP is enabled immediately after AV<sub>IN</sub> passes UVLO level.

Figure 6 illustrates the OCP operation.

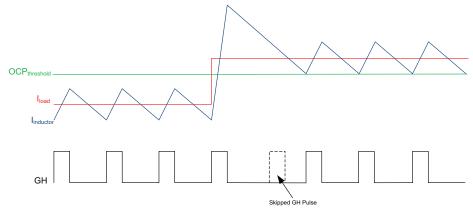


Fig. 6 - Over-Current Protection Illustration

### **Output Under-Voltage Protection (UVP)**

UVP is implemented by monitoring output through  $V_{FB}$  pin. Once the voltage level at  $V_{FB}$  is below 0.45 V for more than 20  $\mu$ s, then UVP event is recognized and both HS and LS MOSFETs are turned off. UVP latches the device off until either  $AV_{IN}$  or EN is recycled.

UVP is only active after the completion of soft-start sequence.

### **Output Over-Voltage Protection (OVP)**

For OVP implementation, output is monitored through FB pin. After soft-start, if the voltage level at FB is above 20 % (typ.), OVP is triggered with HS FET turning off and LS FET turning on immediately to discharge the output. Normal operation is resumed once FB voltage drops back to 0.6 V. OVP is active immediately after AV $_{\rm IN}$  passes UVLO level.

### **Over-Temperature Protection (OTP)**

SiP12017 has internal thermal monitor block that turns off both HS and LS FETs when junction temperature is above 160 °C (typ.). A hysteresis of 30 °C is implemented, so when junction temperature drops below 130 °C, the device restarts by initiating the soft-start sequence again.

### **Soft Startup**

SiP12107 deploys an internally regulated soft-start sequence to realize a monotonic startup ramp without any output overshoot. Once AV $_{\rm IN}$  is above UVLO level (2.55 V typ.). Both the reference and V $_{\rm OUT}$  will ramp up slowly to regulation in 1 ms (typ.) with the reference going from 0 V to 0.6 V and V $_{\rm OUT}$  rising monotonically to the programmed output voltage.

During soft-start period, OCP is activated. OVP and short-circuit protection are not active until soft-start is complete.

## **Pre-bias Startup**

In case of pre-bias startup, output is monitored through FB pin. If the sensed voltage on FB is higher than the internal reference ramp value, control logic prevents HS and LS FET from switching to avoid negative output voltage spike and excessive current sinking through LS FET.

#### Power Good (PG)

SiP12107's Power Good is an open-drain output. Pull PG pin high up to 5 V through a 10K resistor to use this signal. Power Good window is shown in the below diagram. If voltage level on FB pin is out of this window, PG signal is de-asserted by pulling down to GND.

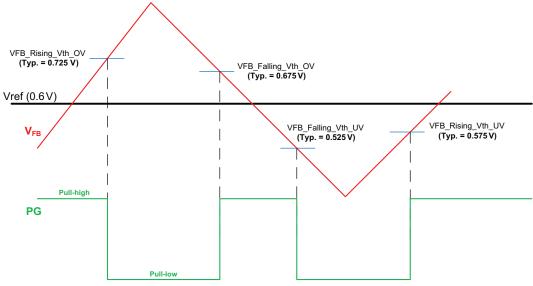


Fig. 7 - PG Window and Timing Diagram

#### **DESIGN PROCEDURE**

The design process of the SiP12107 is quite straight forward. Only few passive components such as output capacitors, inductor and  $R_{\rm on}$  resistor need to be selected.

The following paragraph describes the selection procedure for these peripheral components for a given operating conditions.

In the next example the following definitions apply:

V<sub>INmax.</sub>: the highest specified input voltage

V<sub>INmin.</sub>: the minimum effective input voltage subject to voltage drops due to connectors, fuses, switches, and PCB traces

There are two values of load current to evaluate - continuous load current and peak load current.

Continuous load current relates to thermal stress considerations which drive the selection of the inductor and input capacitors.

Peak load current determines instantaneous component stresses and filtering requirements such as inductor saturation, output capacitors, and design of the current limit circuit.

The following specifications are used in this design:

- $V_{IN} = 3.3 V \pm 10 \%$
- V<sub>OUT</sub> = 1.2 V ± 1 %
- F<sub>SW</sub> = 1 MHz
- Load = 3 A maximum

#### **Setting Switching Frequency**

Selection of the switching frequency requires making a trade-off between the size and cost of the external filter components (inductor and output capacitor) and the power conversion efficiency. The desired switching frequency, 1 MHz was chosen based on optimizing efficiency while maintaining a small footprint and minimizing component cost.

In order to set the design for 1 MHz switching frequency,  $(R_{ON})$  resistor which determines the on-time (indirectly setting the frequency) needs to be calculated using the following equation.

$$R_{ON} = \frac{1}{F_{SW} \times K} = \frac{1}{1 \times 10^6 \times 9.6 \times 10^{-12}} \approx 105 \text{ k}\Omega$$

## **INDUCTOR SELECTION**

In order to determine the inductance, the ripple current must first be defined. Cost, PCB size, output ripple, and efficiency are all used in the selection process. Low inductor values result in smaller size and allow faster transient performance but create higher ripple current which can reduce efficiency. Higher inductor values will reduce the ripple current while compromising the efficiency (higher DCR) and transient response.

The ripple current will also set the boundary for power-save operation. The switcher will typically enter power-save mode when the load current decreases to 1/2 of the ripple current. For example, if ripple current is 1 A then power-save operation will typically start at loads approaching 0.5 A. Alternatively, if ripple current is set at 40 % of maximum load current, then power-save will start for loads less than  $\sim 20$  % of maximum current.

Setting the ripple current 20 % to 50 % of the maximum load current provides an optimal trade-off of the areas mentioned above.

The equation for determining inductance is shown next.

#### Example

In this example, the inductor ripple current is set equal to 30 % of the maximum load current. Thus ripple current will be 30 % x 3 A or 0.9 A. To find the minimum inductance needed, use the  $V_{\text{IN}}$  and  $T_{\text{ON}}$  values that correspond to  $V_{\text{INmax}}$ .

$$L = (V_{IN} - V_{OUT}) \times \frac{T_{ON}}{\Lambda i}$$

Plugging numbers into the above equation we get

$$L \,=\, (3.63 \,V - 1.2 \,V) \,\, x \, \frac{330 \,x \, 10^{-9} \,s}{0.9 \,A} = 0.891 \,\, \mu H$$

A slightly larger value of 1  $\mu$ H is selected which is a standard value. This will decrease the maximum ripple current by 10 %. Note that the inductor must be rated for the maximum DC load current plus 1/2 of the ripple current. The actual ripple current using the chosen 1  $\mu$ H inductor comes out to be.

$$\Delta i = (3.63 \text{ V} - 1.2 \text{ V}) \times \frac{330 \text{ ns}}{1 \mu \text{H}} = 0.8 \text{ A}$$

## **Output Capacitance Calculation**

The output capacitance is usually chosen to meet transient requirements. A worst-case load release, from maximum load to no load at the exact moment when inductor current is at the peak, determines the required capacitance. If the load release is instantaneous (load changes from maximum to zero in <  $1/F_{\rm SW}$  µs), the output capacitor must absorb all the inductor's stored energy. This will approximately cause a peak voltage on the capacitor according to the following equation.

$$C_{OUTmin.} = \frac{L \times \left(I_{OUT} + \frac{1}{2} \times I_{RIPPLEmax.}\right)^{2}}{\left(V_{peak}\right)^{2} - \left(V_{OUT}\right)^{2}}$$

Assuming a peak voltage  $V_{PEAK}$  of 1.3 V (100 mV rise upon load release), and a 3 A load release, the required capacitance is shown by the next equation.

$$C_{OUTmin.} = \frac{1 \mu H \times (3 A + 0.5 \times (81 A))^2}{(1.3 V)^2 - (1.2 V)^2} = 46.37 \mu F$$

If the load release is relatively slow, the output capacitance can be reduced. Using MLCC ceramic capacitors we will use 3 x 22  $\mu$ F or 66  $\mu$ F as the total output capacitance.

#### STABILITY CONSIDERATIONS

Using the output capacitance as a starting point for compensation values. Then, taking Bode plots and transient response measurements we can fine tune the compensation values.

Setting the crossover frequency to 1/5 of the switching frequency:

$$F_0 = F_{sw}/5 = 1 \text{ MHz}/5 = 200 \text{ kHz}$$

Setting the compensation zero at 1/5 to 1/10 the crossover frequency for the phase boost:

$$F_Z = \frac{1}{2\pi \times R_C \times C_C} = \frac{F_0}{5}$$

Setting  $C_C = 1$  nF and solve for  $R_C$ 

$$R_C = \frac{5}{2\pi \, x \, C_C \, x \, F_0} = \frac{5}{2\pi \, x \, 1 \, nF \, x \, 200K} = 4K$$

## **SWITCHING FREQUENCY VARIATIONS**

The switching frequency variation in COT can be mainly attributed to the increase in conduction losses as the load increases. The on time is "ideally constant" so the controller must account for losses by reducing the off time which increases the overall duty cycle. Hence the  $F_{\text{SW}}$  will tend to increase with load.

In power save mode (PSM) the IC will run in pulse skip mode at light loads. As the load increases the  $F_{SW}$  will increase until it reaches the nominal set  $F_{SW}$ . This transition occurs approximately when the load reaches to 20 % of the full load current.

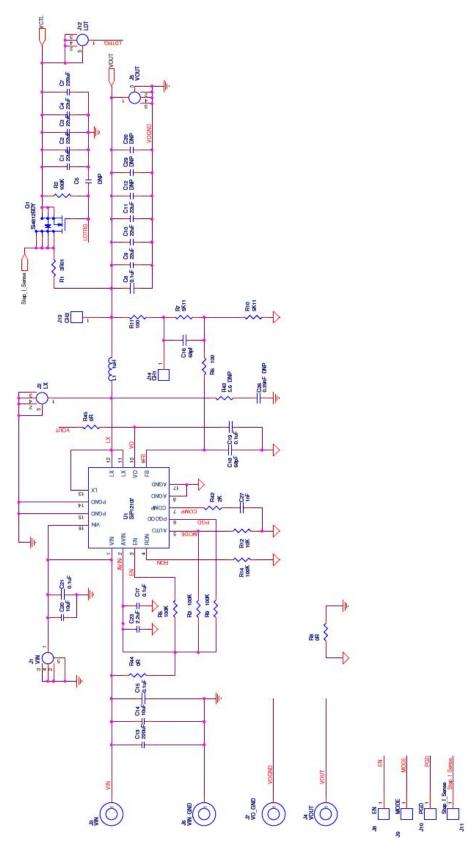


Fig. 8 - Reference Board Schematic



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BILI	BILL OF MATERIALS							
ITEM	QTY.	REFERENCE	PART	VOLTAGE	PCB FOOTPRINT	PART NUMBER	MANUFACTURER	
1	4	C1, C2, C3, C4	22 µF	16 V	SM/C_1210	GRM32ER71C226ME18L	Murata	
2	1	C5	DNP	50 V	SM/C_0603	-	-	
3	2	C7, C13	220 μF	25 V	594D-R TYPE	594D227X0016R2T	Vishay	
4	3	C8, C19, C21	0.1 μF	50 V	SM/C_0603	VJ0603Y104KXACW1BC	Vishay	
5	3	C9, C10, C11	22 µF	6.3 V	SM/C_1210	GCM32ER70J476KE19L	Murata	
6	3	C12, C29, C30	DNP	6.3 V	SM/C_1210	-	-	
7	2	C14, C20	10 μF	16 V	SM/C_1206	C1206C106K4RACTU	Taiyo Yuden	
8	1	C15	0.1 μF	50 V	SM/C_0402	VJ0603Y104KXACW1BC	Vishay	
9	1	C16	68 pF	50 V	SM/C_0603	VJ0402A680JNAAJ	Vishay	
10	1	C17	0.1 µF	50 V	SM/C_0402	VJ0402Y104KXACW1BC	Vishay	
11	1	C18	68 pF	50 V	SM/C_0402	VJ0402A680JNAAJ	Vishay	
12	1	C23	2.2 µF	10 V	SM/C_0603	GRM188R71A225KE15D	Murata	
13	1	C26	DNP	50 V	SM/C_0402	-	-	
14	1	C27	1 nF	50 V	SM/C_0402	VJ0402Y102KXACW1BC	Vishay	
29	1	L1	1μH	-	IHLP2525	IHLP2525DZER1R0M01	Vishay	
30	1	Q1	-	30 V	SO-8	Si4812BDY	Vishay	
31	1	R1	3R01	200 V	C_2512	CRCW25123R01FKTA	Vishay	
32	4	R2, R3, R5, R9	100K	50 V	SM/C_0603	CRCW0603100KFKEA	Vishay	
33	1	R6	100	50 V	SM/C_0402	TNPW0402100RBEED	Vishay	
34	1	R7	5K11	50 V	SM/C_0603	CRCW06035K11FKEA	Vishay	
35	1	R8	0R	50 V	SM/C_0402	CRCW04020000FKTA	Vishay	
36	1	R10	5K11	-	SM/C_0603	CRCW06035K11FKEA	-	
37	1	R11	100	50 V	SM/C_0603	TNPW0402100RBEED	Vishay	
38	1	R12	10K	50 V	SM/C_0603	CRCW060310K0FKEA	Vishay	
39	1	R14	100K	50 V	SM/C_0603	CRCW0603100KFKEA	Vishay	
40	1	R42	2K	50 V	SM/C_0603	CRCW06032K00FKEA	Vishay	
41	1	R43	DNP	-	SM/C_0805	-		
42	1	R44	0R	50 V	SM/C_0603	CRCW06030000Z0EA	Vishay	
43	1	R45	0R	50 V	SM/C_0402	CRCW04020000FKTA	Vishay	
44	1	U1	-	-	QFN3X3_16 L	SiP12107	Vishay	
45	1	J1	V <sub>IN</sub>		PROBE PIN	PK007-015	Lecroy	
46	1	J2	LX		PROBE PIN	PK007-015	Lecroy	
47	1	J3	V <sub>IN</sub>		Power connector	575-6	Keystone	
48	1	J4	V <sub>OUT</sub>		Power connector	575-6	Keystone	
49	1	J5	V <sub>OUT</sub>		PROBE PIN	PK007-015	Lecroy	
50	1	J6	V <sub>IN</sub> GND		Power connector	575-6	Keystone	
51	1	J7	V <sub>O</sub> _GND		Power connector	575-6	Keystone	
52	1	J8	EN		Control PIN	1573-3	Keystone	
53	1	J9	MODE		Control PIN	1573-3	Keystone	
54	1	J10	PGD		Probe PIN	1573-3	Keystone	
55	1	J11	Step_I_Sense		Probe PIN	1573-3	Keystone	
56	1	J12	LDT		SMA test connector	PK007-015	Lecroy	
57	1	J13	CH2		Test point	1573-3	Keystone	
58	1	J14	CH1		Test point	1573-3	Keystone	



## **PCB LAYOUT OF REFERENCE BOARD**

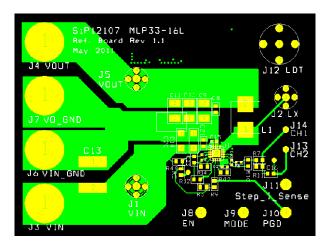


Fig. 9 - Top Layer

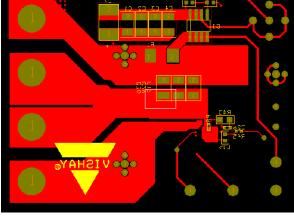


Fig. 11 - Bottom Layer

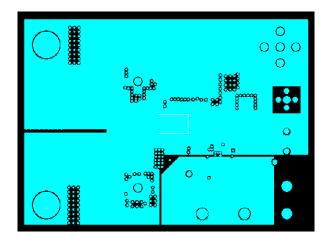


Fig. 10 - Inner Layer1

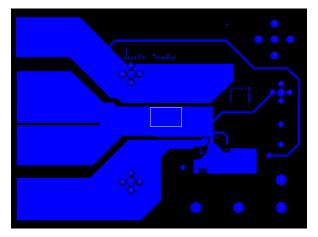


Fig. 12 - Inner Layer2

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